

SiC Schottky Barrier Rectifier

Features

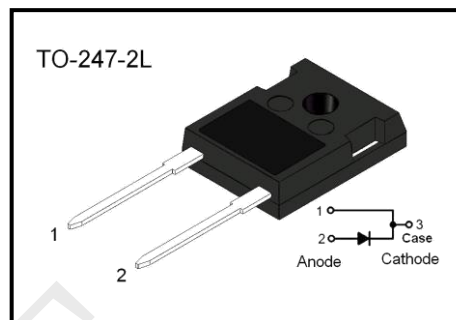
- Reverse withstand voltage 1200V
- Zero reverse recovery current
- High working frequency
- Switch characteristics are not affected by temperature
- Fast switching speed
- Positive temperature coefficient of positive pressure drop

Advantages

- Very low switching loss
- Higher efficiency
- Low dependence of the system on the heat sink
- No thermal collapse in parallel devices

Application

- Switching mode power supply, AC/DC converter
- Power factor correction
- Motor drive
- PV inverter and wind turbine



Absolute Maximum Rating (Ta=25°C)

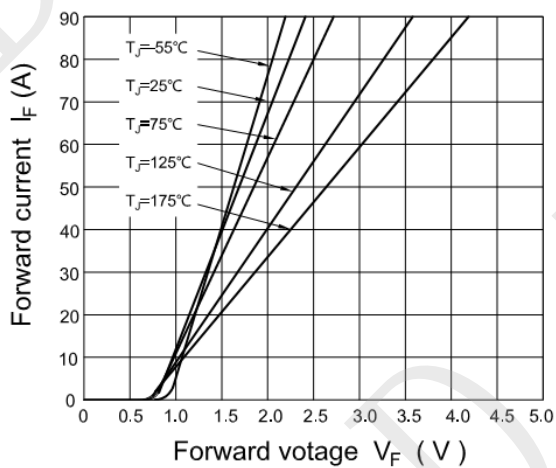
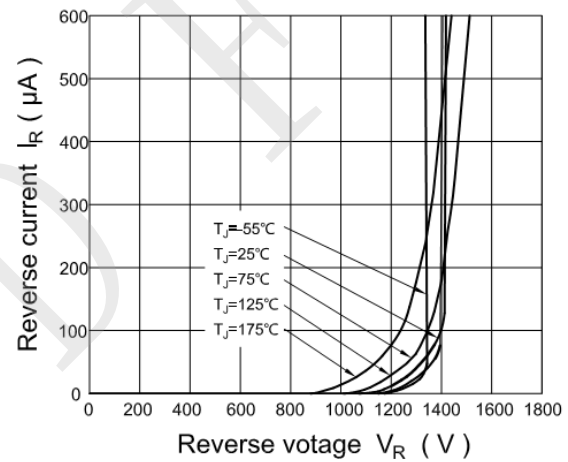
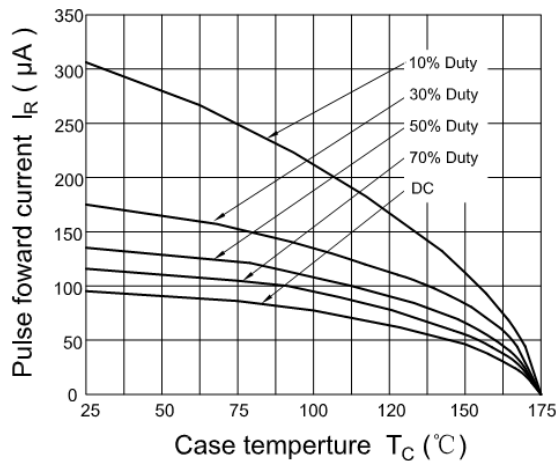
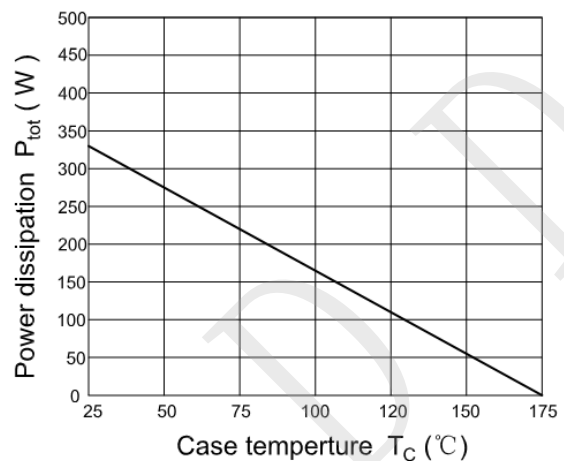
Parameter	Symbol	Test conditions	Value	Unit
Peak repetitive reverse voltage	V_{RRM}		1200	V
Working peak reverse voltage	V_{RWM}		1200	V
DC blocking voltage	V_{DC}		1200	V
Average rectified output current	$I_{F(AV)}$	$T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$ $T_C = 150^\circ\text{C}$	85 38 30	A
Forward repetitive peak current	I_{FRM}	$T_C = 25^\circ\text{C}$, tp=10ms, Half Sine Wave $T_C = 110^\circ\text{C}$, tp=10ms, Half Sine Wave	118 62	A
Forward surge current	I_{FSM}	$T_C = 25^\circ\text{C}$, tp=10ms, Half Sine Wave $T_C = 110^\circ\text{C}$, tp=10ms, Half Sine Wave	175 125	A
Power dissipation	P_{tot}	$T_C = 25^\circ\text{C}$ $T_C = 110^\circ\text{C}$	328 151	W
Junction temperature	T_j		-55 ~ +175	°C
Storage temperature	T_{stg}		-55 ~ +175	°C
Mounting torque		M3 Screw 6-32 Screw	1 8.8	Nm lbf-in

Thermal characteristics

Parameter	Symbol	Vaule	Unit
Thermal resistance - junction to case	$R_{\theta JC}$	0.45	°C/W

Electrical Characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 30\text{ A}$, $T_J = 25^\circ\text{C}$ $I_F = 30\text{ A}$, $T_J = 175^\circ\text{C}$		1.5 2.2	1.8 3.0	V
Reverse current	I_R	$V_R = 1200\text{V}$, $T_J = 25^\circ\text{C}$ $V_R = 1200\text{V}$, $T_J = 175^\circ\text{C}$		35 65	200 400	μA
Total capacitive charge	Q_C	$V_R = 400\text{V}$, $I_F = 10\text{A}$ $di/dt = 500\text{A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		152		nC
Total capacitance	C	$V_R = 0\text{V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{MHz}$ $V_R = 200\text{V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{MHz}$ $V_R = 400\text{V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{MHz}$		2177 136 100		pF

Typical Characteristics

Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics

Figure 3. Current Derating

Figure 4. Power Derating

Typical Characteristics

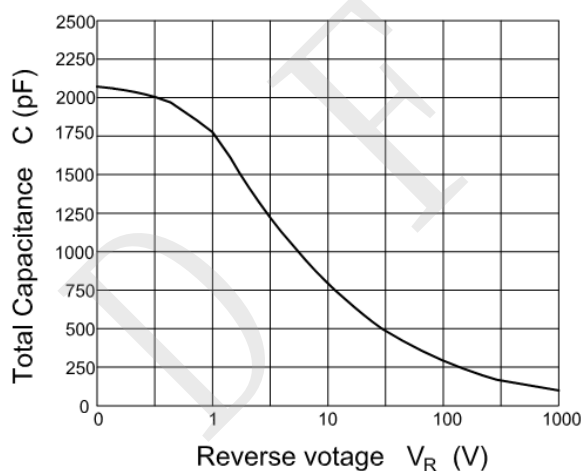


Figure 5. Capacitance vs reverse voltage

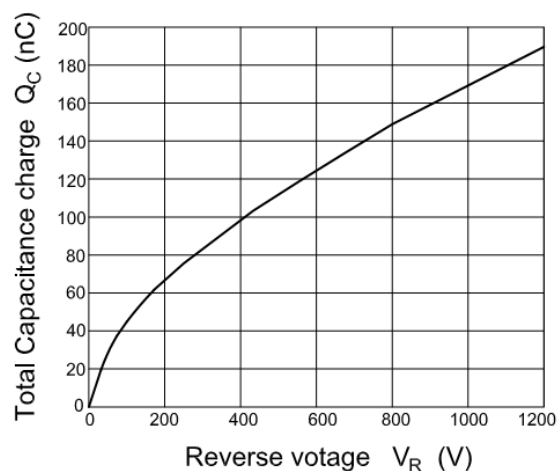
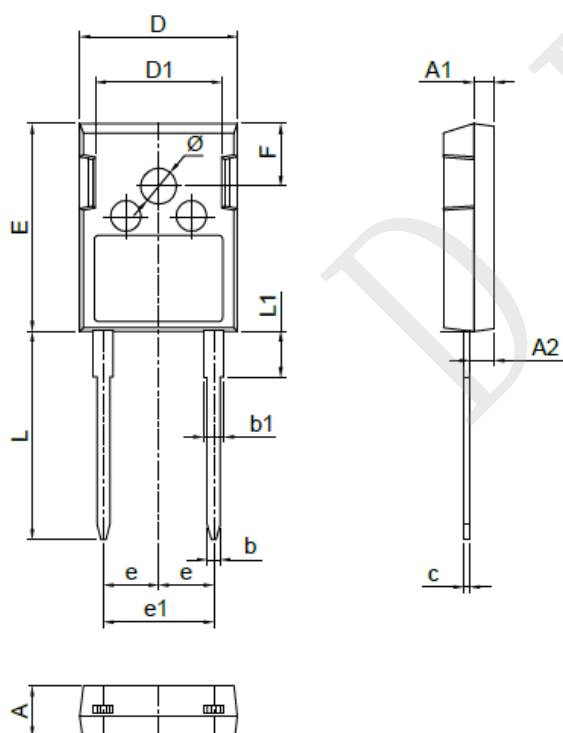


Figure 6. Total Capacitance charge vs. reverse voltage

Package Dimensions



Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	1.90	2.10	0.075	0.083
A2	2.29	2.54	0.090	0.100
b	1.00	1.40	0.039	0.055
b1	2.00	2.20	0.079	0.087
c	0.50	0.70	0.020	0.028
D	15.75	16.05	0.620	0.632
E	20.20	20.80	0.795	0.819
e	5.45 (BSC)		0.215 (BSC)	
F	6.05	6.25	0.238	0.246
F1	5.80	6.00	0.228	0.236
L	20.10	20.40	0.791	0.803
L1	4.05	4.35	0.159	0.171
Φ	3.50	3.70	0.138	0.146